



Erratum

Direct Patterning of Low-*k* Hydrogen Silsesquioxane Using X-Ray Exposure Technology [Electrochemical and Solid-State Letters, 6, G69 (2003)]

**T. C. Chang,^{a,c} T. M. Tsai,^b P. T. Liu,^c Y. S. Mor,^b C. W. Chen,^b J. T. Sheu,^d
and T. Y. Tseng^b**

^a*Department of Physics, National Sun Yat-Sen University, Kaohsiung, Taiwan*

^b*Institute of Electronics, National Chiao Tung University, Hsin-Chu, Taiwan*

^c*National Nano Device Laboratory, Hsin-Chu 300, Taiwan*

^d*Department of Electrical Engineering, National Chi Nan University, Puli-Nantou, Taiwan 545*

© 2003 The Electrochemical Society. [DOI: 10.1149/1.1576571] All rights reserved.
Available electronically April 21, 2003.

The “Acknowledgments” section on page G71 (left-hand column), should read:

The authors thank Dow-Corning Taiwan, Inc., for providing the HSQ solution. This work was performed at National Nano Device Laboratory and was supported by the Synchrotron Radiation Research Center in Hsin Chu, R.O.C., and the National Science Council of the Republic of China under contract no. NSC91-2112-M-110-008.